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Optical and Quantum Electronics
Volume 50, Issue 9, 1 September 2018, Article number 346

Volume of precursor solution effect on the properties of SnO₂ thin films prepared by nebulized spray pyrolysis technique(Article)

Palanichamy, S., Raj Mohamed, J., Satheesh Kumar, P.S., Pandiarajan, S., Amalraj, L.

^aResearch Department of Physics, V.H.N.S.N. College, Virudhunagar, Tamilnadu 626001, India

^bResearch Department of Physics, H.H. The Rajah's College, Pudukkottai, Tamilnadu 622001, India

^cDepartment of Physics, Devanga Arts College, Aruppukottai, Tamilnadu 626101, India

Abstract

Undoped SnO₂ thin films have been deposited on amorphous glass substrates with different precursor solution volume (10, 15, 20 and 25 ml) using simple and cost-effective nebulized spray pyrolysis technique. The influence of precursor solution on structural, optical, photoluminescence and electrical properties had been studied. The X-ray diffraction spectra prove the polycrystalline nature of SnO₂ with tetragonal structure. All the films show a preferred growth orientation along (110) diffraction plane. The average transmittance of SnO₂ thin films varied between 82 and 75% in the visible as well as IR region. The band gap energy decreases from 3.74 to 3.64 eV corresponding to direct transitions with the precursor solution volume had increased from 10 to 20 ml and then increased as 3.72 eV for 25 ml. SEM pictures demonstrated polyhedrons like grains. EDX confirmed the existence of Sn and O elements in all the prepared SnO₂ thin films. Photoluminescence spectra at room temperature revealed that the four emission bands in all the samples such as sharp dominant peak at 361 nm with shoulder peak at 377 nm (UV region), a broad and low intensity peak at 492 nm (blue region) and 519 nm (green region). The electrical parameters were examined by Hall effect measurements, which demonstrated that the film prepared at 20 ml precursor solution volume possess minimum resistivity $2.76 \times 10^{-3} \Omega\text{-cm}$ with activation energy 0.10 eV and maximum figure of merit $1.54 \times 10^{-2} (\Omega/\text{sq})^{-1}$. © 2018, Springer Science+Business Media, LLC, part of Springer Nature.

Author keywords

[Activation energy](#) [Band gap](#) [Crystallite size](#) [Nebulized spray pyrolysis](#) [Tin oxide](#)

Indexed keywords

Engineering controlled terms:

[Activation energy](#) [Amorphous films](#) [Amorphous materials](#) [Cost effectiveness](#) [Crystallite size](#)
[Energy gap](#) [Film preparation](#) [Photoluminescence](#) [Solution mining](#) [Spray pyrolysis](#)
[Substrates](#) [Tin oxides](#)

Engineering uncontrolled terms

[Different precursors](#) [Electrical parameter](#) [Hall effect measurement](#) [Nebulized spray pyrolysis](#)
[Photoluminescence spectrum](#) [Precursor solutions](#) [Tetragonal structure](#)
[X-ray diffraction spectrum](#)

Engineering main heading:

[Thin films](#)

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